

3D Interfacial Delamination Near Solder Bumps in Flip-Chip Package

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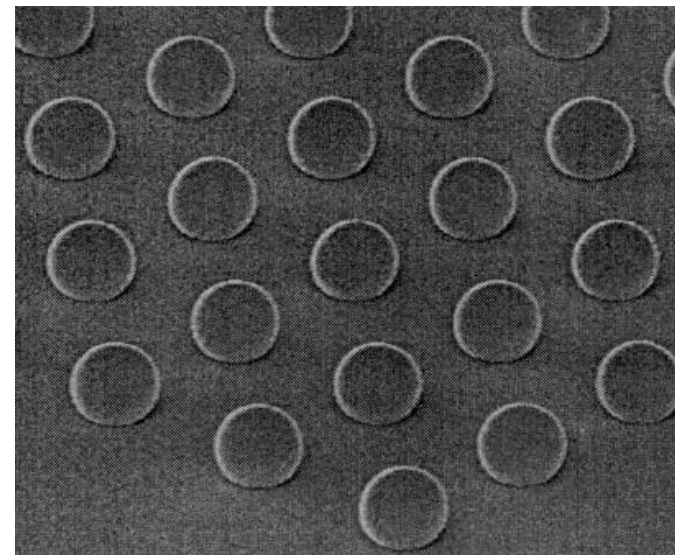
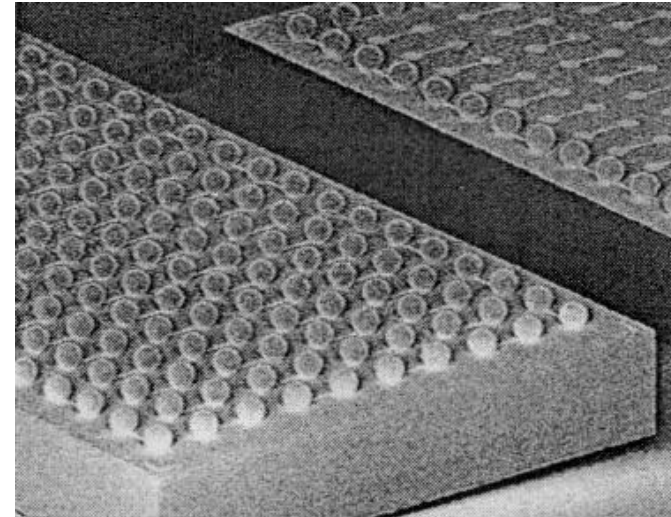
Symposium on 3D Fracture

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Objectives

- ❑ Utilize global/local modeling to investigate delamination characteristics of flip chips.
- ❑ Quantify the differences between 2D approximation and real 3D structures.
- ❑ Identify potential fracture modes and likely delamination sites near solder bumps.
- ❑ Determine fracture parameters along 3D delamination fronts.
- ❑ Use 3D model to estimate fatigue life of solder bumps in flip chip packages.

Solder Bumps (~100 μ m dia)



(Microfab Technology. Singapore)

Earlier Works

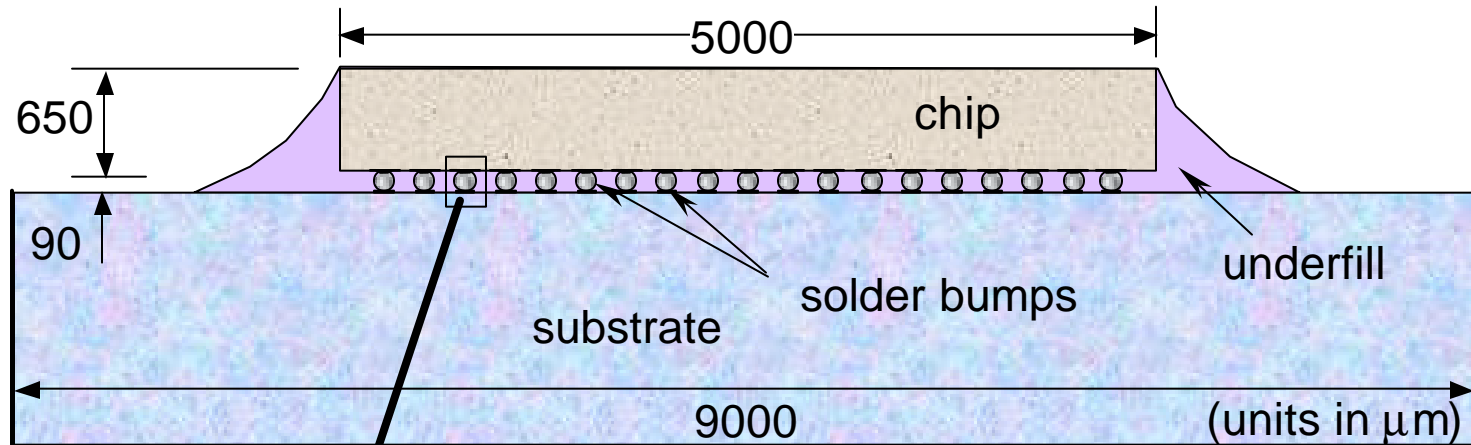
- Understanding roles of underfill materials and interface reliability. *Rzepka et al.*, 1998.
- Optimization of interconnect structure — solder joints. *Wiegele et al.*, 1998.
- Thermal fatigue life estimation in 2D/3D models. *Lau*, 1993; *Paydar et al.*, 1994; *Gektin et al.*, 1997; *Hong, et al.*, 1997.
- Fracture behaviors and effects of process-induced stresses under real loading history with temperature and time-dependent materials. *Gall et al.*, 1996; *Wang et al.*, 1998.
- Global-local analysis. *Burattynski*, 1992; *Zhu et al.*, 1997; *Madenci et al.*, 1998.

Present Analysis

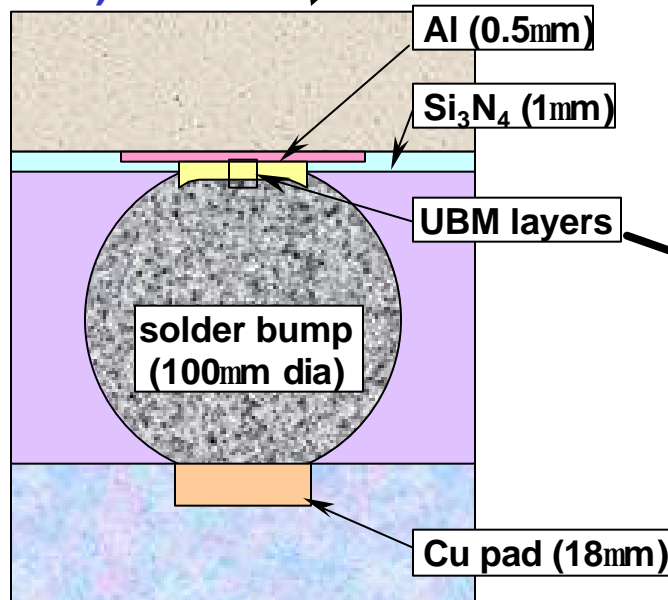
- Multi-scale (global/local) procedure is adopted to model extreme size differences among various components.
- Regions of high stress concentration are identified (e.g., likely failure sites).
- Fracture parameters are determined in complex 3D models.
- Fatigue-life is estimated from cyclic thermal loading.

Multi-Scale FE Analysis (cross-sectional views)

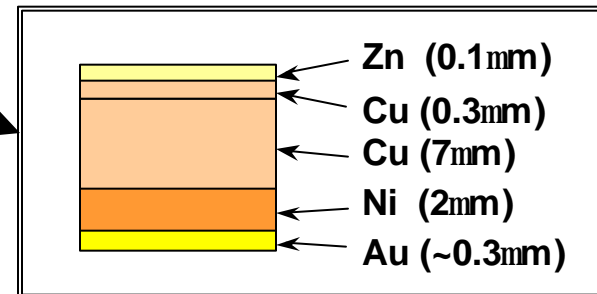
Flip-chip package (*global model*)



Solder bump region (*cell model*)



Under bump metallurgy



Boundary and Load Conditions

- Temperature drop from 155°C to 20°C.
- Global Model: constrain displacements of symmetry and bottom planes in the direction perpendicular to themselves.
- Cell Model: prescribed displacements along the perimeter of cell model — *interpolated from the global analysis.*

Assumption: 1) *no initial residual stresses*; 2) *no transient heat transfer*; 3) *uniform temperature distribution*; 4) *gradually applied loads.*

Material Properties

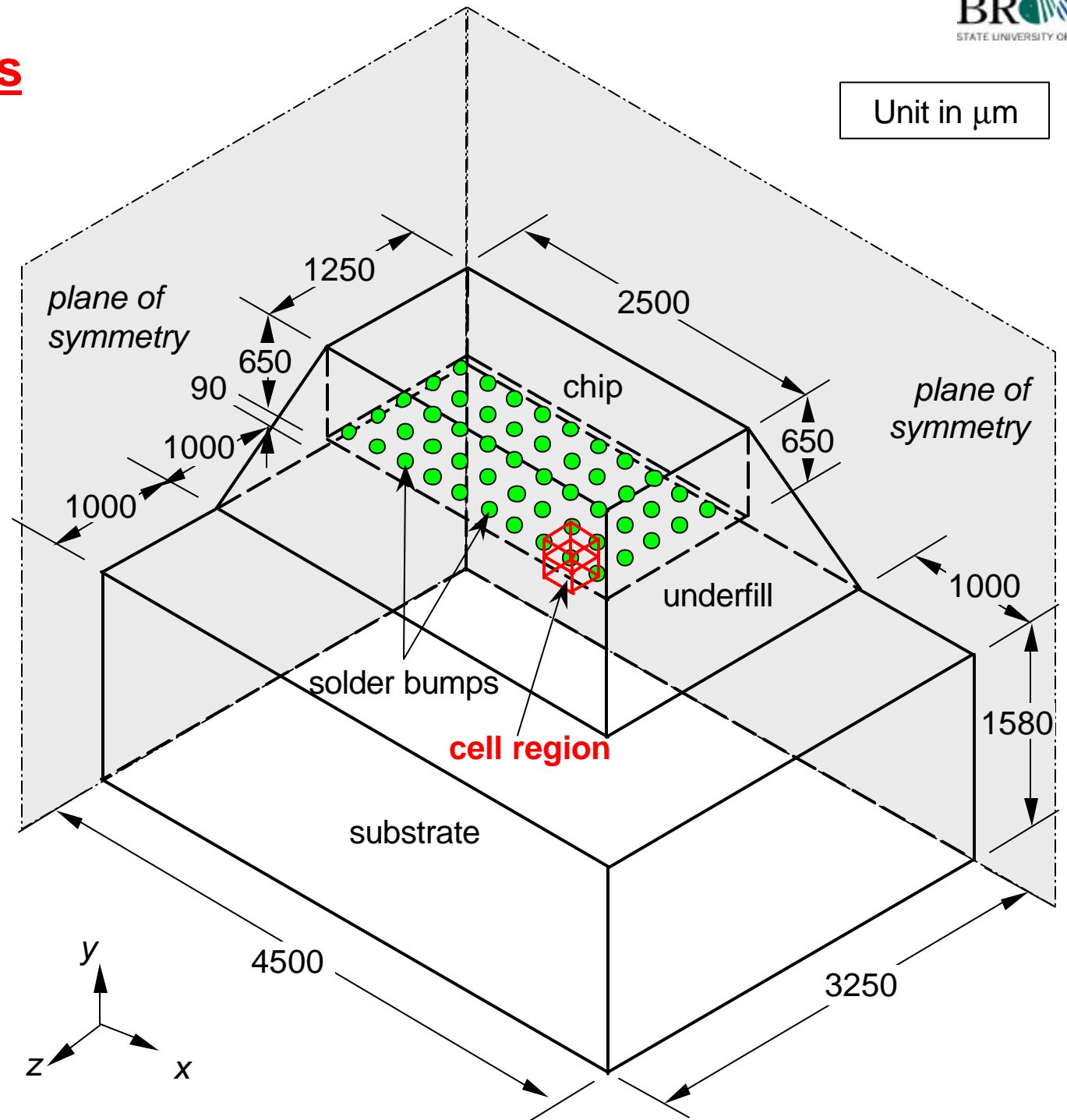
Materials	CTE ($10^{-6}/^{\circ}\text{C}$)	E (GPa)	n	S_o (MPa)
chip (Si)	2.8	131	0.30	
passivation (Si_3N_4)	2.9	325	0.24	
bond pad (Al)	23.2	70	0.24	
UBM layer 1 (Cu)	16	117	0.30	
UBM layer 2 (Ni)	12.7	200	0.31	
solder bump (63Sn/37Pb)	21	30	0.35	20
underfill	33	8.5	0.28	
substrate	18	22	0.28	

3D Global Analysis

Unit in μm

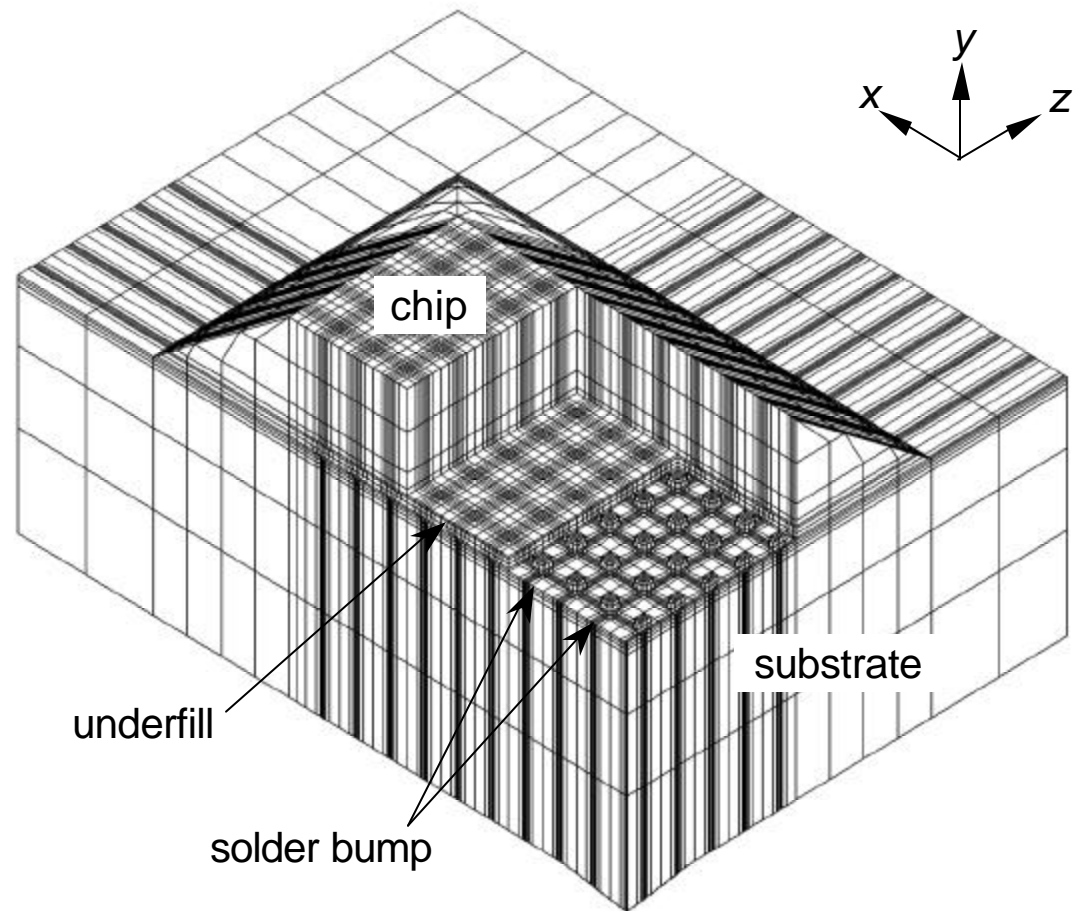
one quarter of the flip-chip package

- *Underfill between chip and substrate for adhesion.*
- *50 solder bumps are individually modeled.*



3D Global Mesh

- *51,675 eight-node isoparametric brick elements.*
- *45 cell regions containing solder bump and Cu pad.*



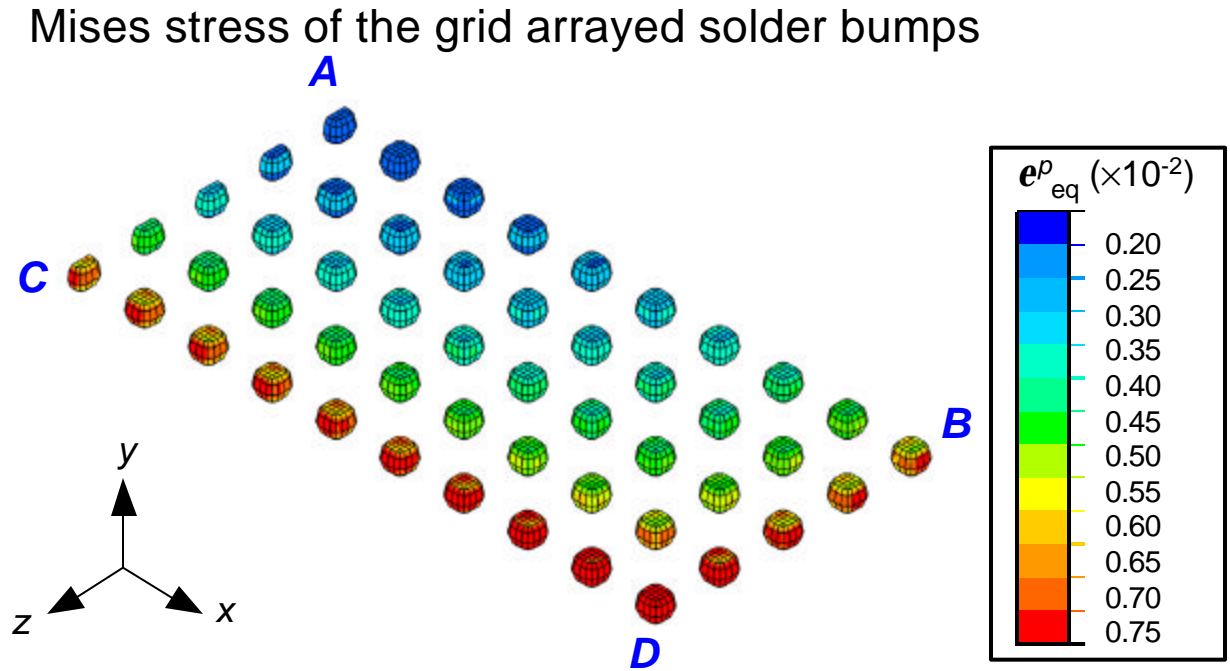
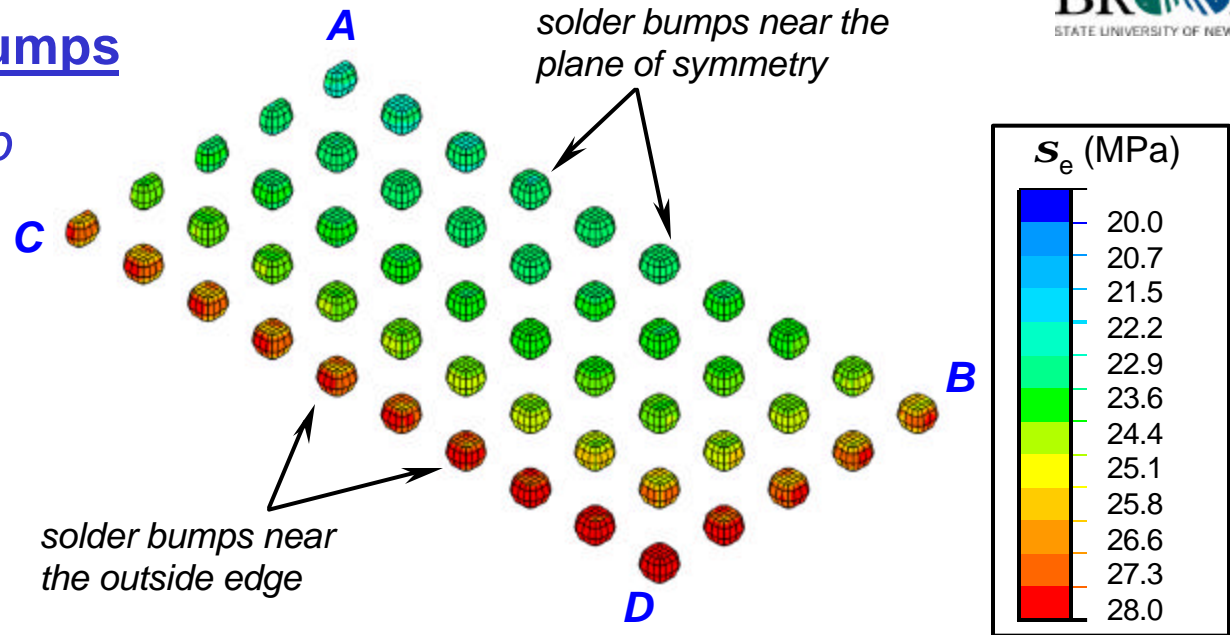
(b)

Stresses of Various Solder Bumps

P determination of critical bump

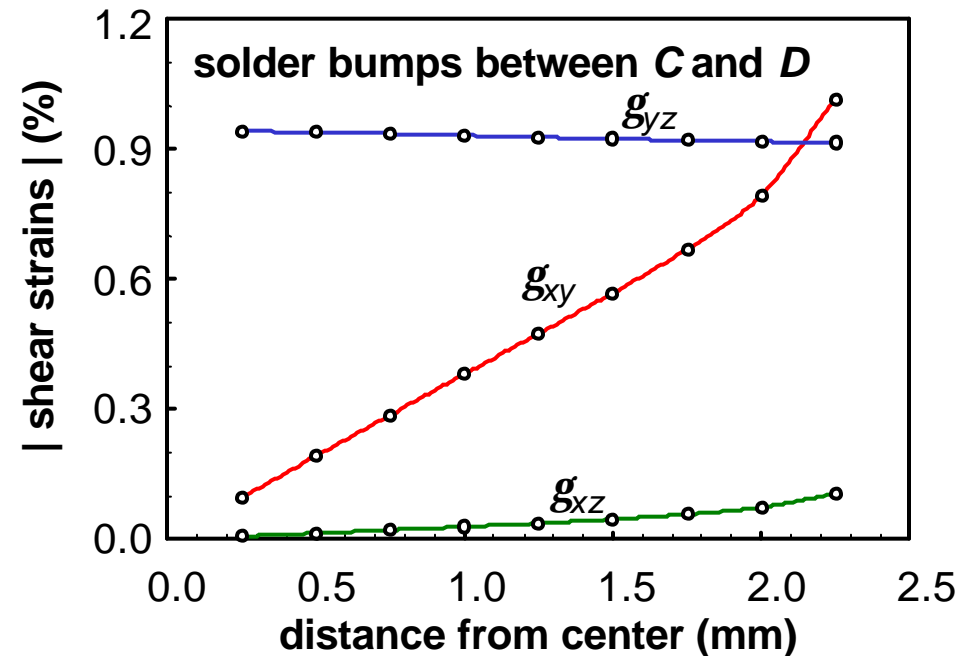
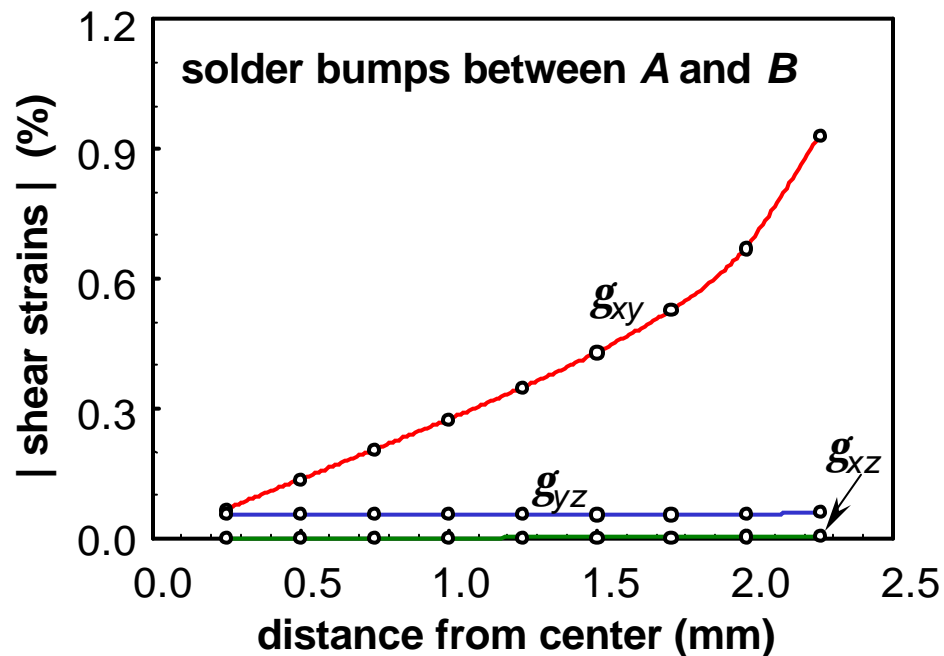
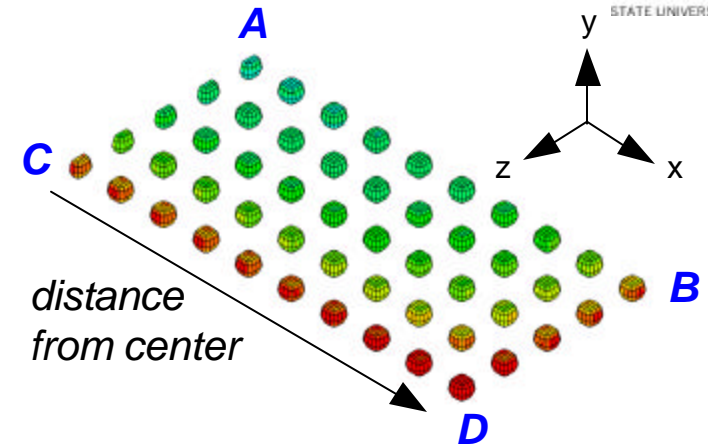
Loading Condition
 $DT = -135^{\circ}C$

- Greater stresses are observed for solder bumps further away from the symmetry planes.
- Large stress concentration between underfill and chip along edges.



Average Shear Strains in Solder Bumps

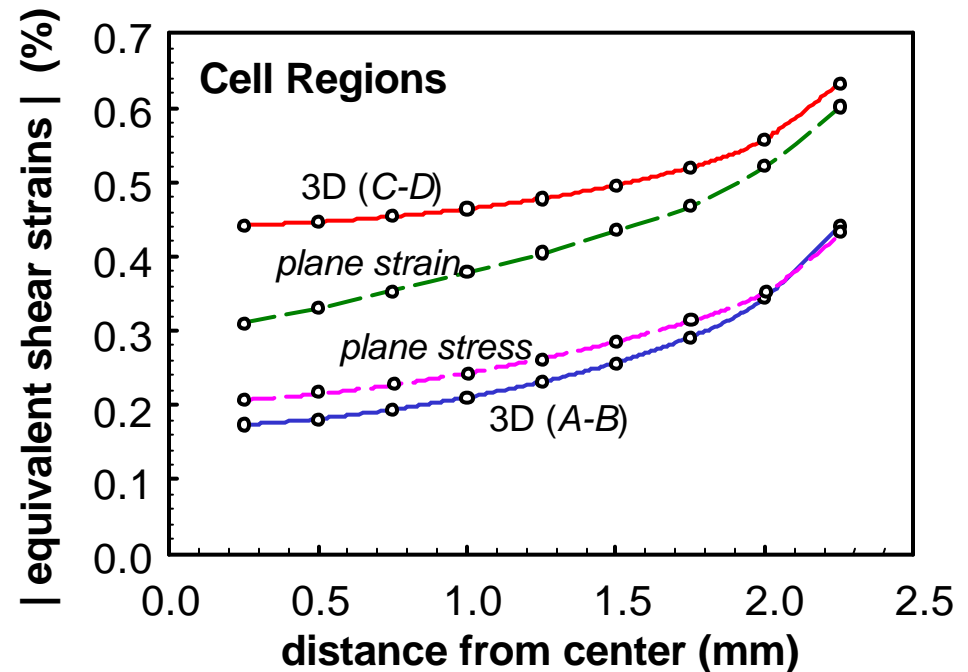
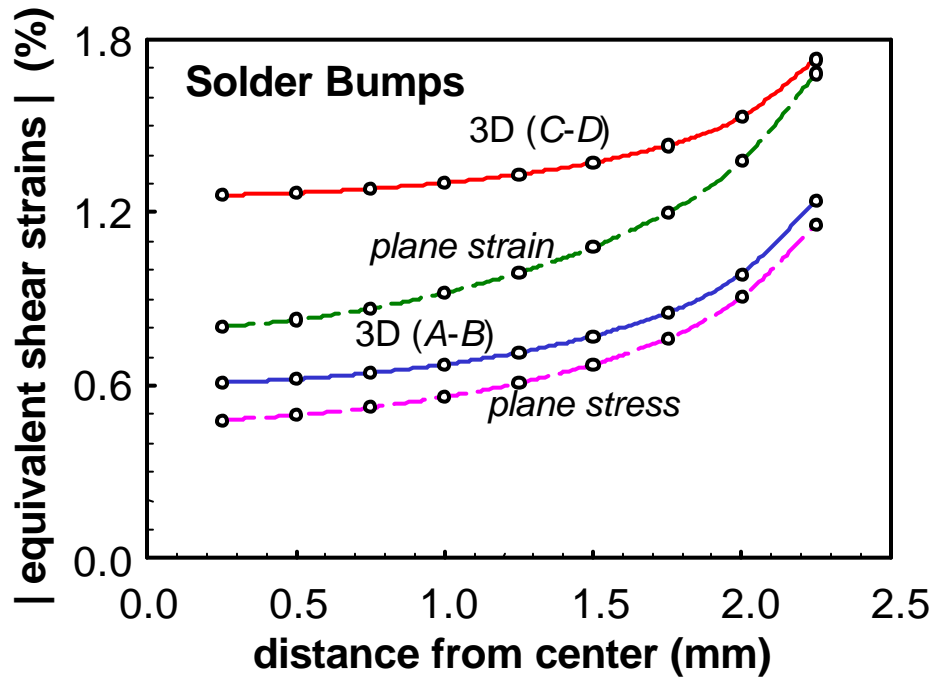
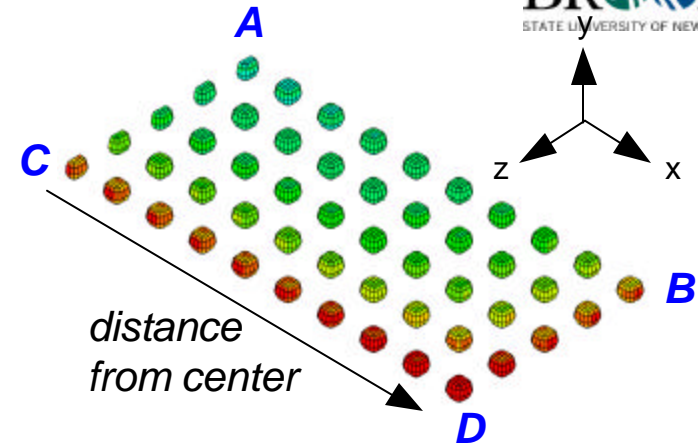
- Increasing shear strain from center to the edge.
- Out-of-plane shear strain is larger near the edge.



Comparison with 2D Models

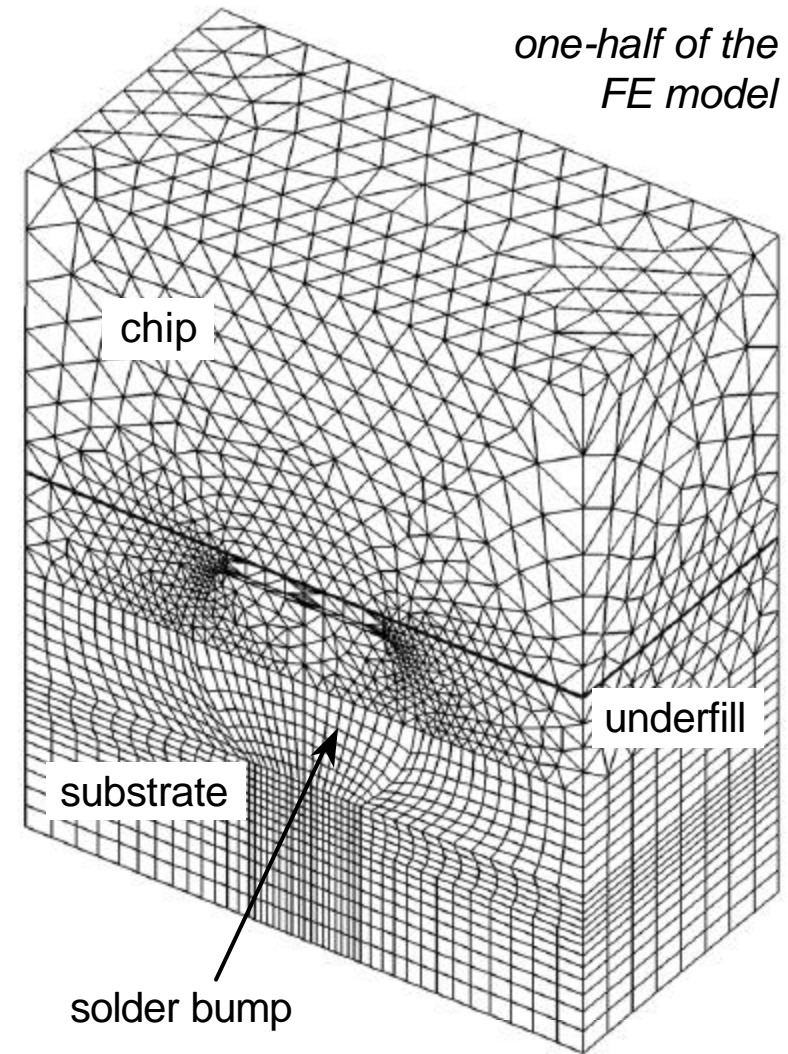
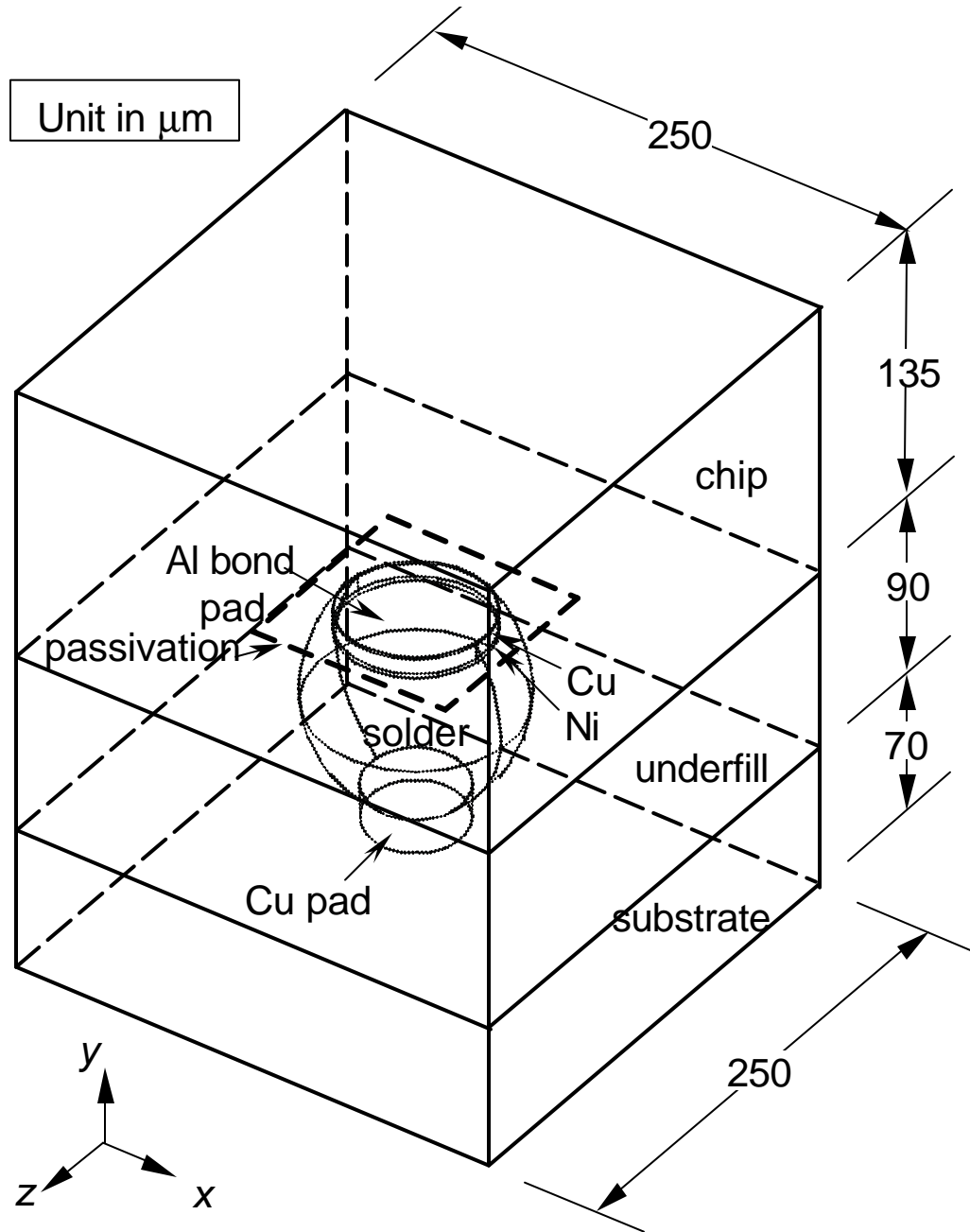
Equivalent Shear Strains:

$$\epsilon_{eq} = \sqrt{\frac{2}{3} \left[(\epsilon_x - \epsilon_y)^2 + (\epsilon_y - \epsilon_z)^2 + (\epsilon_z - \epsilon_x)^2 + \frac{3}{2} (g_{xy}^2 + g_{xz}^2 + g_{zx}^2) \right]}^{1/2}$$



- 3D equivalent shear strain is greater than plane strain and plane stress results.
- Out-of-plane shear contributes to higher equivalent shear strains in 3D model.

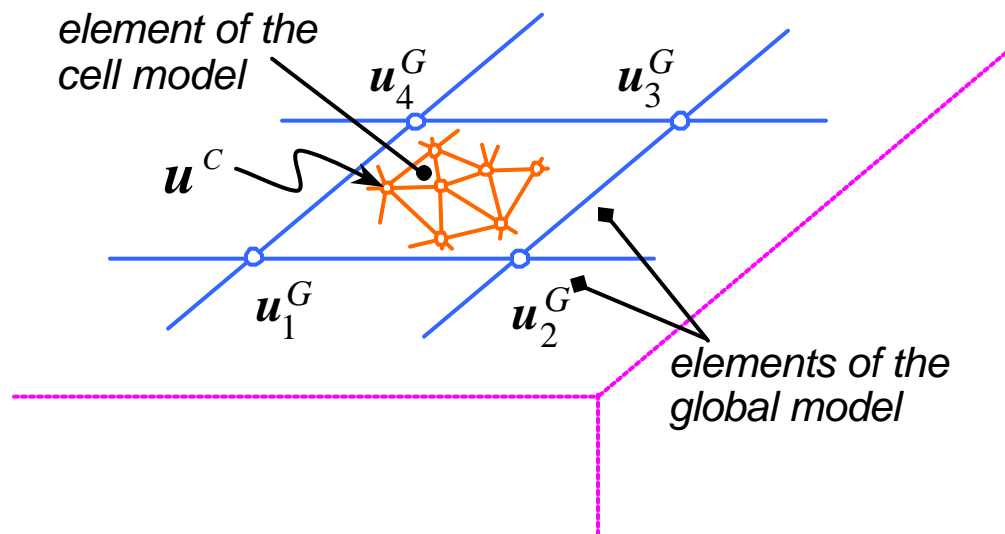
3D Cell Analysis



About 70,000 four-node tetrahedron and 20,000 eight-node brick elements

Boundary/Loading Condition for Cell Model

Displacement solutions from global model are prescribed to surface nodes of cell model using interpolation functions.



$$\mathbf{u}^C = \sum_{a=1}^4 N_a(\mathbf{x}, \mathbf{h}) \mathbf{u}_a^G$$

\mathbf{u}^C : aimed nodal displacements
of the cell model

\mathbf{u}_a^G : known nodal displacements
of the global model

N_a : shape functions

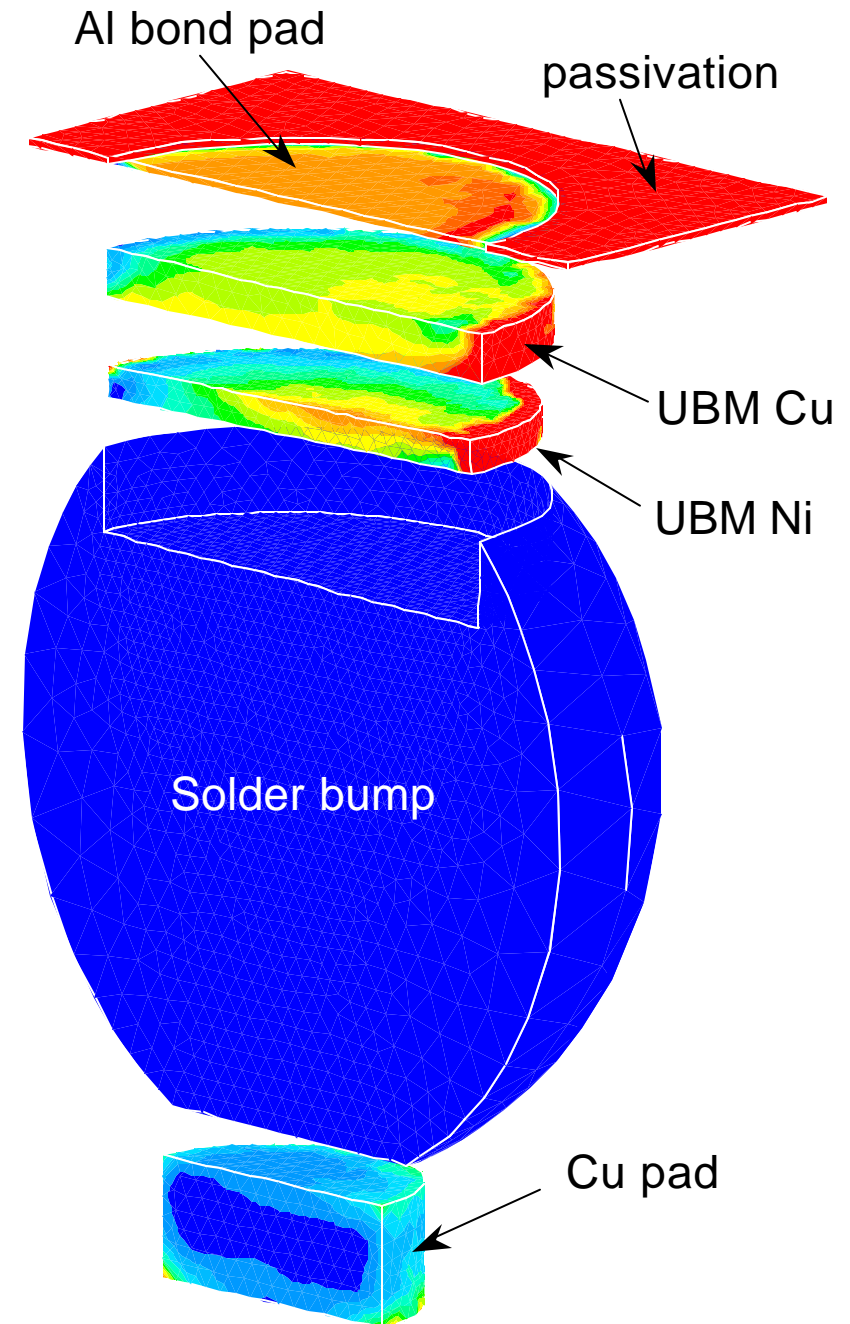
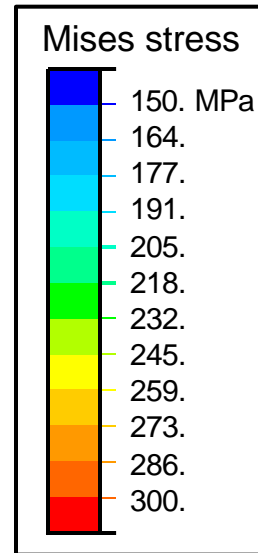
\mathbf{x}, \mathbf{h} : local coordinates

*Interpolations are carried out
for six surfaces of cell models*

Stresses near Solder Bump

P determination of critical interfaces

- *Stress remains low in solder due to plastic flow.*
- *Stress concentration occurs at interfaces of solder bump and UBM (Ni and Cu).*
- *Large stress is also observed near Cu pad.*



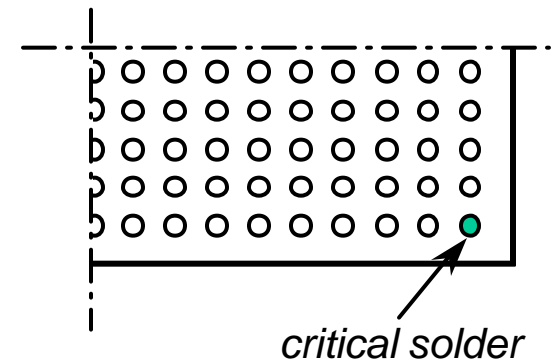
3D Fracture Analysis

- Detailed 3D model to identify fracture behavior.
- Comparison with 2D fracture results.

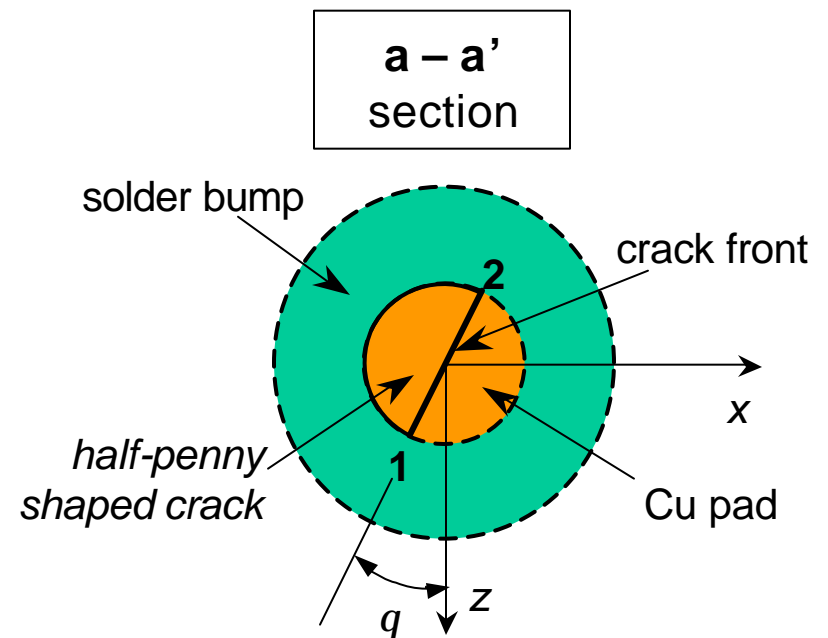
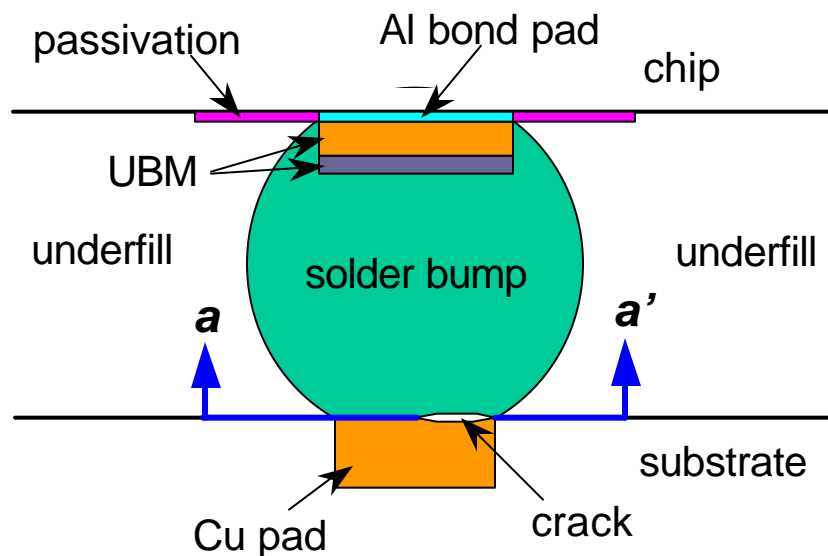
Fracture parameters to be determined

Energy Release Rate — J

$$\text{Phase Angle } \gamma \approx \tan^{-1} \left(\frac{\mathbf{s}_{xy}}{\mathbf{s}_{yy}} \right), \quad \mathbf{f} \approx \cos^{-1} \left| \frac{\mathbf{s}_{yz}}{\sqrt{\mathbf{s}_{yy}^2 + \mathbf{s}_{xy}^2 + \mathbf{s}_{yz}^2}} \right|$$

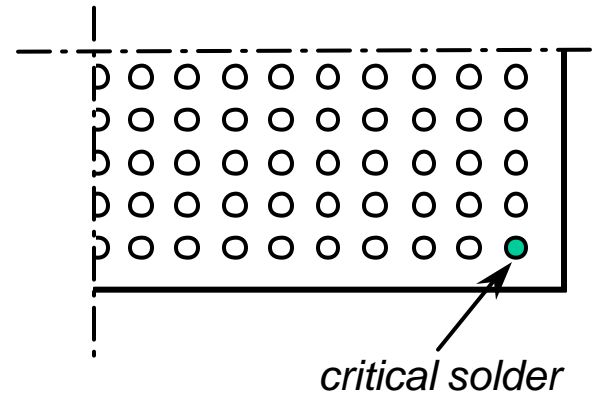
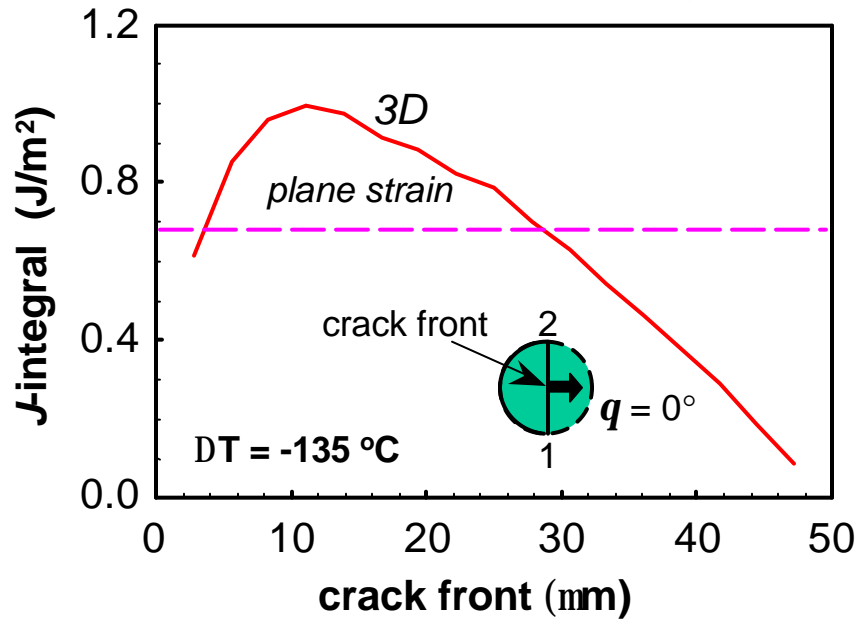


Half penny shaped crack

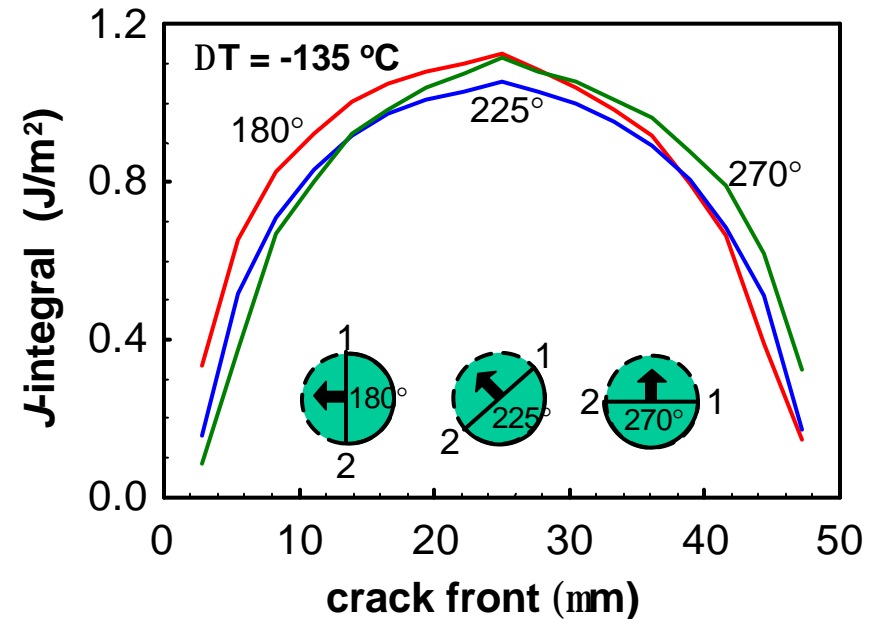
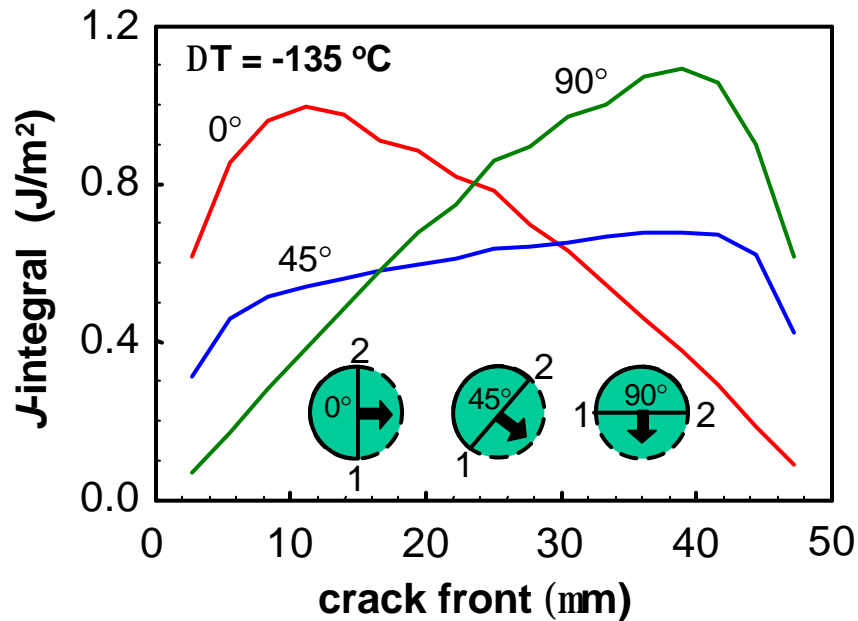


J-integral for 3D interfacial crack front

between solder bump and CU pad



Phase angle of the straight crack front when $q = 0^\circ$ is $\gamma = 30^\circ \sim 35^\circ$, $f = 65^\circ \sim 70^\circ$; For the plane strain case, $\gamma \sim 55^\circ$.



Fatigue Life Estimation

Coffin-Manson law

Mean cycle to fail for near eutectic Sn-Pb solder :

$$N_f = \frac{1}{2} \left(\frac{\Delta \mathbf{g}}{2 \mathbf{e}_f} \right)^{\frac{1}{c}}$$

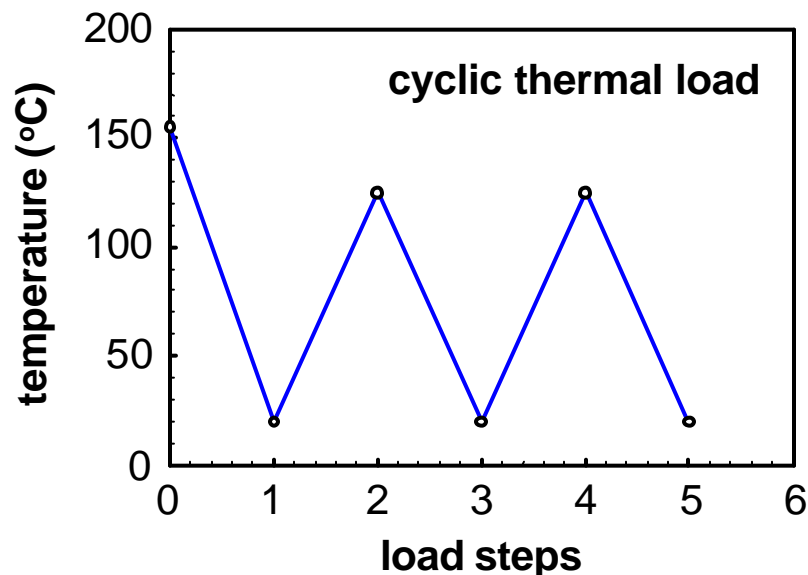
$e_f = \text{fatigue ductility coefficient} = 0.325$

$c = \text{fatigue ductility exponent} = -0.5$

Equivalent shear strain :

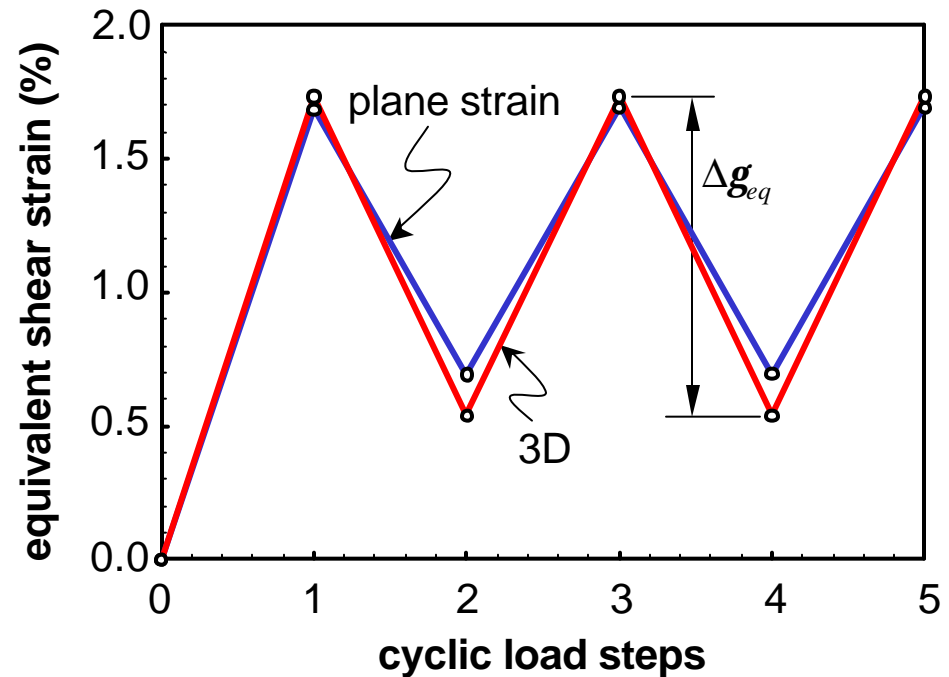
$$\mathbf{g} = \sqrt{\frac{2}{3}} \left[(\mathbf{e}_x - \mathbf{e}_y)^2 + (\mathbf{e}_y - \mathbf{e}_z)^2 + (\mathbf{e}_z - \mathbf{e}_x)^2 + \frac{3}{2} (\mathbf{g}_{xy}^2 + \mathbf{g}_{yz}^2 + \mathbf{g}_{zx}^2) \right]^{\frac{1}{2}}$$

Cyclic thermal load:



Comparison between 2D and 3D Results

Average equivalent shear strains within solder bumps



Thermal fatigue life :

Load steps	Temperature (°C)	3D		Plane strain	
		Average $\Delta\gamma$ (%)	Maximum $\Delta\gamma$ (%)	Average $\Delta\gamma$ (%)	Maximum $\Delta\gamma$ (%)
1	155 → 20	1.73	2.02	1.68	1.94
2	20 → 125	1.10	1.27	0.82	1.01
3	125 → 20	1.10	1.27	0.83	0.98
4	20 → 125	1.10	1.27	0.82	0.97
5	125 → 20	1.10	1.27	0.82	0.97
Fatigue life N_f		2728	2020	5058	3486

Kinematic Hardening Solder Model

Thermal fatigue life :

Load steps	Temperature (°C)	3D		Plane strain	
		Average $\Delta\gamma$ (%)	Maximum $\Delta\gamma$ (%)	Average $\Delta\gamma$ (%)	Maximum $\Delta\gamma$ (%)
1	155 → 20	1.73	2.02	1.68	1.87
2	20 → 125	1.19	1.39	0.99	1.13
3	125 → 20	1.19	1.38	1.00	1.11
4	20 → 125	1.19	1.38	1.00	1.11
5	125 → 20	1.19	1.38	1.00	1.11
Fatigue life N_f		2301	1691	3356	2663

Kinematic hardening solder : *Lshikawa et al. (1994); Basaran & Tang (2002).*

Summary

- ❑ Detailed 3D local analysis are carried out based on the global 3D analysis. Results are compared with 2D models.
- ❑ **Large stress** are observed in the flip-chip package for solder bumps and nearby interfaces away from the symmetry planes. **Equivalent shear strain** is greater than those of plane strain and plane stress cases.
- ❑ High stress concentration is observed at interfaces between **solder bump** and **UBM** as well as between **solder bump** and **Cu pad**.
- ❑ 3D fracture analyses show a **non-uniform** distribution of energy release rate. The magnitude of J along some part of crack front is higher than that of plane strain J .
- ❑ 3D fatigue life estimation suggests a **shorter fatigue life** than the one assumed from the plane strain analysis.

Flip-Chip Procedure

1. Al metallization — termination pad
2. Passivation coating — insulating/protection
3. Etch/form a hole through passivation and cleaning
4. Deposition of UBM
5. Add solder bump/paste and reflow
6. Flip the chip to the solder pasted substrate
7. Reflow
8. Test and wafer dicing
9. Encapsulation — underfill dispense
10. Curing
11. Final inspection